## NSN 5962-01-391-2513

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View Online at https://aerobasegroup.com/nsn/5962-01-391-2513
Maximum Power Dissipation Rating:
550.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
End Application:
Cv-3993/sys-2 e/i fscm 21877
Features Provided:
Programmed and electrostatic sensitive
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Case Outline Source And Designator:
D-9 mil-m-38510
Product Name:
2k x 8 bit, prom
Voltage Rating And Type Per Characteristic:
4.5 volts applied and 5.5 volts applied
Time Rating Per Chacteristic:
35.00 nanoseconds af output megawatts
Memory Device Type:
Prom
Hybrid Technology Type:
Monolithic
Special Features:
One time programmable
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883
standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit
Specification Data:
67268-5962-88734 government standard
Specification Or Standard:
03 type and I case and a finish
Departure From Cited Designator:
Programmed per: 301018 (21877)
Shelf Life:

Demilitarization:

**Unit Of Measure:** 

N/a

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